

FIG.1A
CONVENTIONAL ART

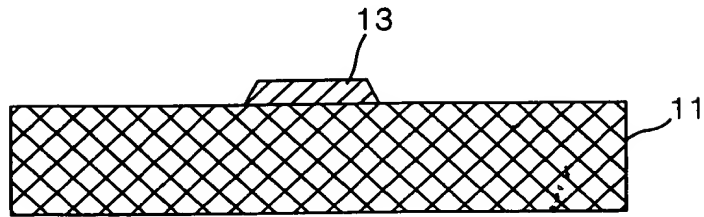


FIG.1B
CONVENTIONAL ART

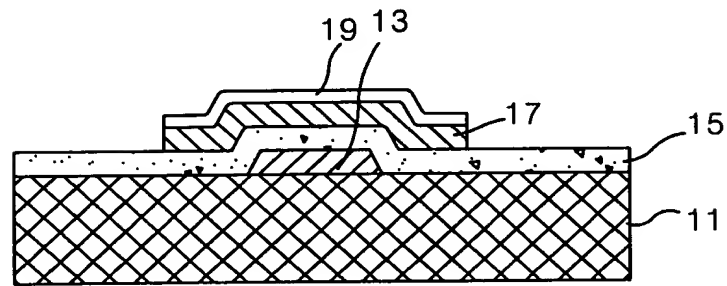


FIG.1C
CONVENTIONAL ART

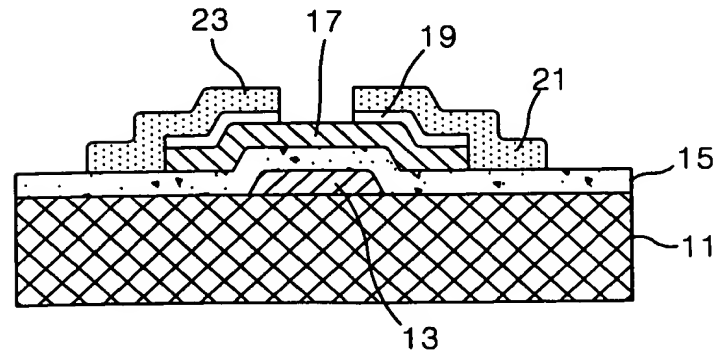


FIG.1D
CONVENTIONAL ART

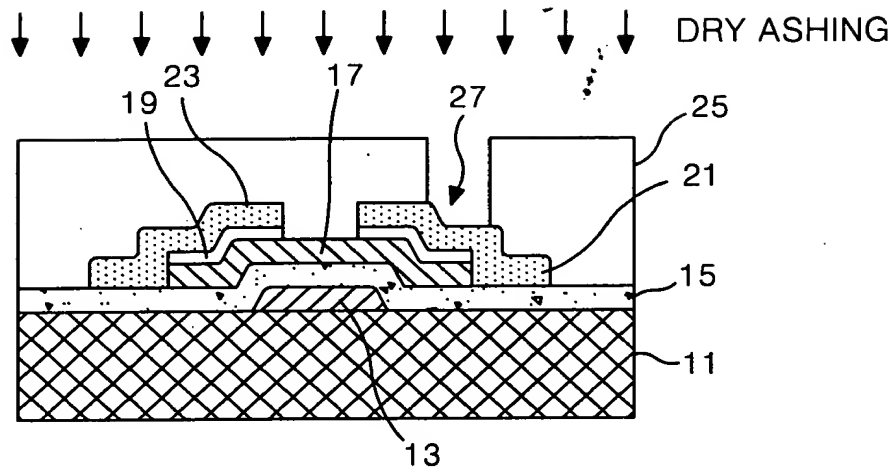
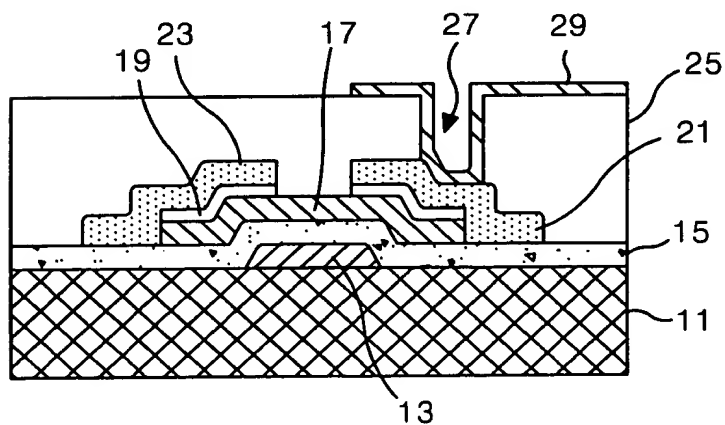
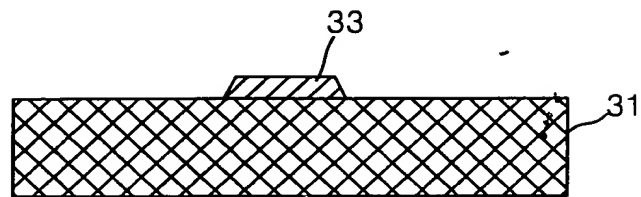


FIG.1E
CONVENTIONAL ART



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A cross-sectional view of a semiconductor device. It features a substrate 31 with a cross-hatched pattern. A thin layer 35 is deposited on top of the substrate. A patterned layer 37 is formed on the thin layer 35, with a central opening 33. A top layer 39 is deposited on the patterned layer 37, filling the opening 33.

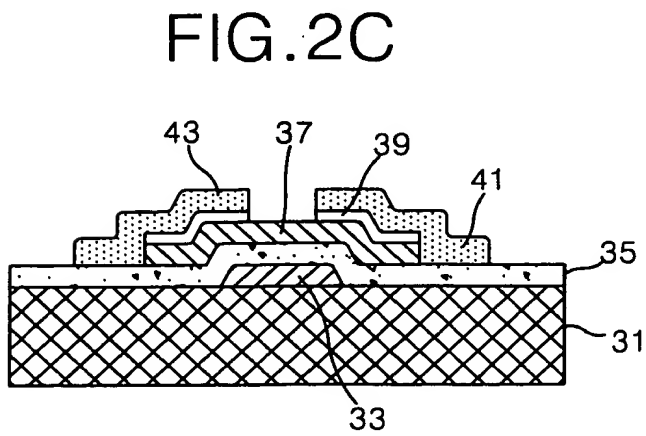


FIG.2D

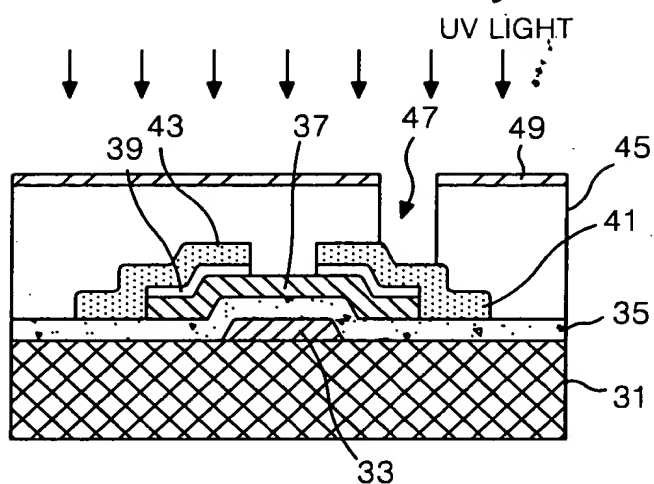


FIG.2E

